



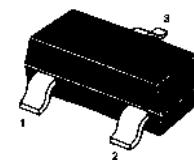
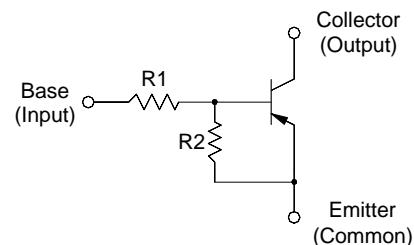
**迈拓电子**  
MAITUO ELECTRONIC

## PNP Silicon Epitaxial Planar Transistor

for switching and interface circuit and  
drive circuit applications

### Resistor Values

Type	R1 (K)	R2 (K)
MMUN2111	10	10
MMUN2112	22	22
MMUN2113	47	47
MMUN2114	10	47
MMUN2115	10	$\infty$
MMUN2116	4.7	$\infty$
MMUN2130	1	1
MMUN2131	2.2	2.2
MMUN2132	4.7	4.7
MMUN2133	4.7	47
MMUN2134	22	47



1.Base 2.Emitter 3.Collector  
SOT-23 Plastic Package

### DEVICE MARKING AND RESISTOR VALUES

Device	Package	Marking	R1 (K)	R2 (K)	Shipping
MMUN2111	SOT-23	A6A	10	10	3000/Tape & Reel
MMUN2112	SOT-23	A6B	22	22	3000/Tape & Reel
MMUN2113	SOT-23	A6C	47	47	3000/Tape & Reel
MMUN2114	SOT-23	A6D	10	47	3000/Tape & Reel
MMUN2115	SOT-23	A6E	10	$\infty$	3000/Tape & Reel
MMUN2116	SOT-23	A6F	4.7	$\infty$	3000/Tape & Reel
MMUN2130	SOT-23	A6G	1.0	1.0	3000/Tape & Reel
MMUN2131	SOT-23	A6H	2.2	2.2	3000/Tape & Reel
MMUN2132	SOT-23	A6J	4.7	4.7	3000/Tape & Reel
MMUN2133	SOT-23	A6K	4.7	47	3000/Tape & Reel
MMUN2134	SOT-23	A6L	22	47	3000/Tape & Reel

### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	50	V
Collector Emitter Voltage	$-V_{CEO}$	50	V
Collector Current	$-I_C$	100	mA
Total Power Dissipation	$P_{tot}$	200	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_s$	- 55 to + 150	$^\circ\text{C}$



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### Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE} = 10 \text{ V}$ , $-I_C = 5 \text{ mA}$	$h_{FE}$	35	-	-
		60	-	-
		80	-	-
		80	-	-
		160	-	-
		160	-	-
		3	-	-
		8	-	-
		15	-	-
		80	-	-
Collector Base Cutoff Current at $-V_{CB} = 50 \text{ V}$	$-I_{CBO}$	-	100	nA
Collector Emitter Cutoff Current at $-V_{CE} = 50 \text{ V}$	$-I_{CEO}$	-	500	nA
Emitter Base Cutoff Current at $-V_{EB} = 6 \text{ V}$	$-I_{EBO}$	-	0.5	
		-	0.2	
		-	0.1	
		-	0.2	
		-	0.9	
		-	1.9	mA
		-	4.3	
		-	2.3	
		-	1.5	
		-	0.18	
		-	0.13	
Collector Base Breakdown Voltage at $-I_C = 10 \mu\text{A}$	$-V_{(BR)CBO}$	50	-	V
Collector Emitter Breakdown Voltage at $-I_C = 2 \text{ mA}$	$-V_{(BR)CEO}$	50	-	V
Collector Emitter Saturation Voltage at $-I_C = 10 \text{ mA}$ , $-I_B = 0.3 \text{ mA}$ at $-I_C = 10 \text{ mA}$ , $-I_B = 5 \text{ mA}$	$-V_{CEsat}$	-	0.25	
		-	0.25	
		-	0.25	
		-	0.25	
		-	0.25	
		-	0.25	V
		-	0.25	



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**Characteristics at  $T_a = 25^\circ\text{C}$**

Parameter	Symbol	Min.	Max.	Unit
Output Voltage (on) at $-V_{CC} = 5 \text{ V}$ , $-V_B = 2.5 \text{ V}$ , $R_L = 1 \text{ k}\Omega$	$-V_{OL}$	-	0.2	V
MMUN2111				
MMUN2112				
MMUN2114				
MMUN2115				
MMUN2116				
MMUN2130				
MMUN2131				
MMUN2132				
MMUN2133				
MMUN2134				
at $-V_{CC} = 5 \text{ V}$ , $-V_B = 3.5 \text{ V}$ , $R_L = 1 \text{ k}\Omega$				
MMUN2113				
Output Voltage (off)	$-V_{OH}$	4.9	-	V
at $-V_{CC} = 5 \text{ V}$ , $-V_B = 0.5 \text{ V}$ , $R_L = 1 \text{ k}\Omega$				
MMUN2130				
at $-V_{CC} = 5 \text{ V}$ , $-V_B = 0.05 \text{ V}$ , $R_L = 1 \text{ k}\Omega$				
MMUN2115				
at $-V_{CC} = 5 \text{ V}$ , $-V_B = 0.25 \text{ V}$ , $R_L = 1 \text{ k}\Omega$				
MMUN2116	$R_1$	4.9	-	$\text{k}\Omega$
MMUN2131				
MMUN2132				
MMUN2133				
MMUN2134				
Input Resistor	$R_1$	7	13	$\text{k}\Omega$
MMUN2111				
MMUN2112				
MMUN2113				
MMUN2114				
MMUN2115				
MMUN2116				
MMUN2130				
MMUN2131				
MMUN2132				
Resistor Ratio	$R_1/R_2$	0.8	1.2	-
MMUN2111/MMUN2112/MMUN2113				
MMUN2114				
MMUN2115/MMUN2116				
MMUN2130/MMUN2131/MMUN2132				
MMUN2133	$R_1/R_2$	0.17	0.25	-
	$R_1/R_2$	-	-	-
	$R_1/R_2$	0.8	1.2	-
	$R_1/R_2$	0.055	0.185	-



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TYPICAL ELECTRICAL CHARACTERISTICS  
MMUN2111

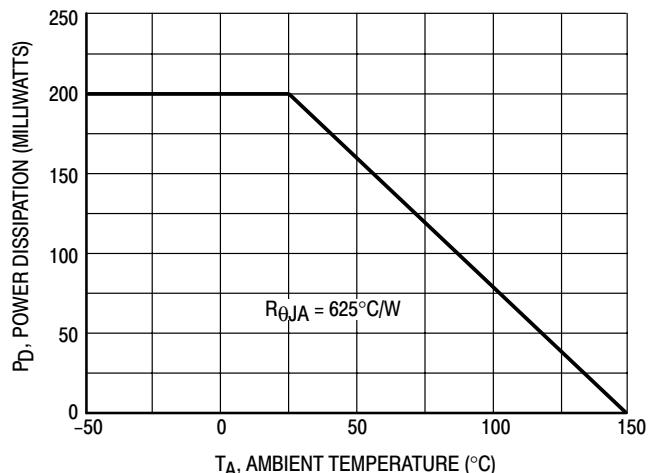


Figure 1. Derating Curve

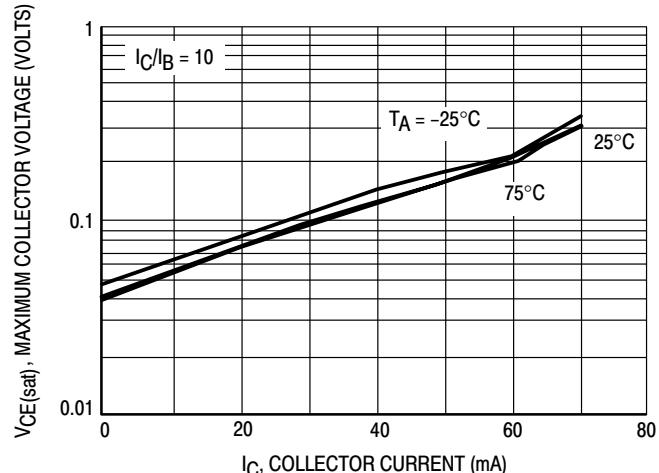


Figure 2.  $V_{CE(\text{sat})}$  versus  $I_C$

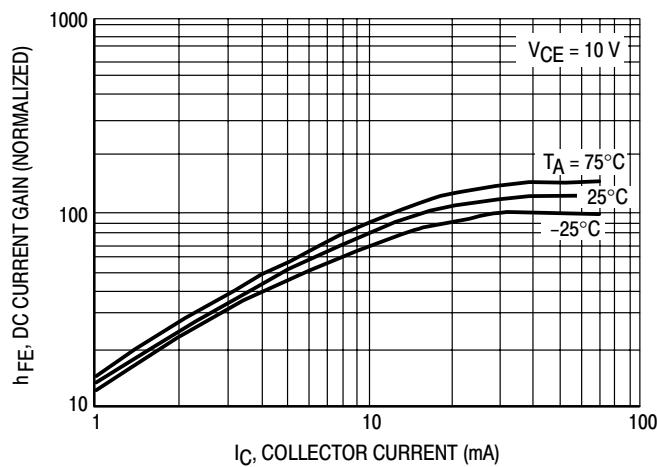


Figure 3. DC Current Gain

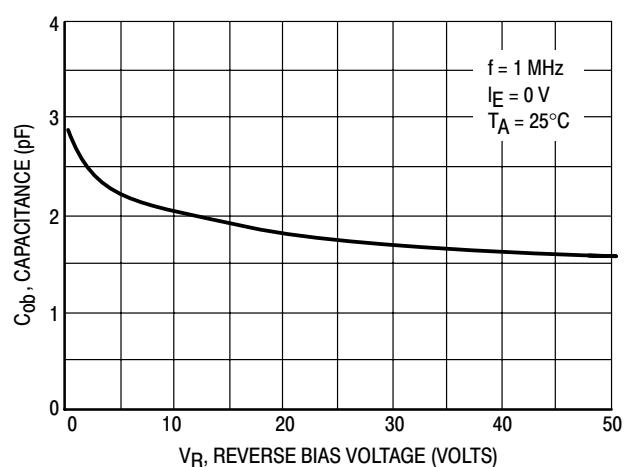


Figure 4. Output Capacitance

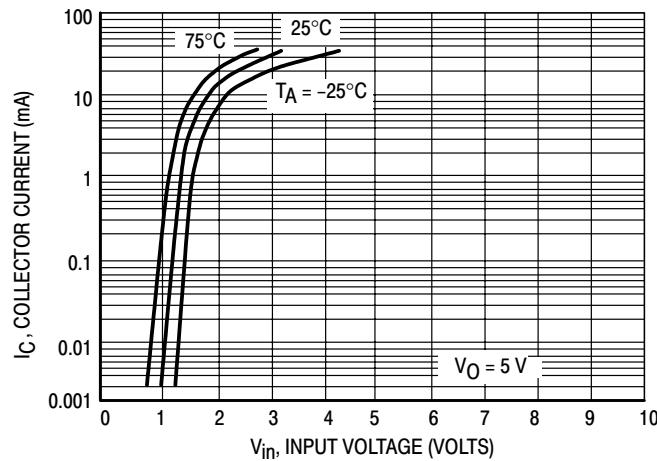


Figure 5. Output Current versus Input Voltage

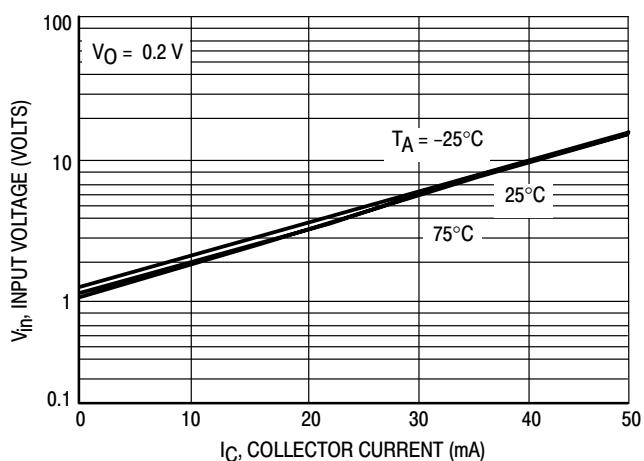


Figure 6. Input Voltage versus Output Current



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MMUN2112

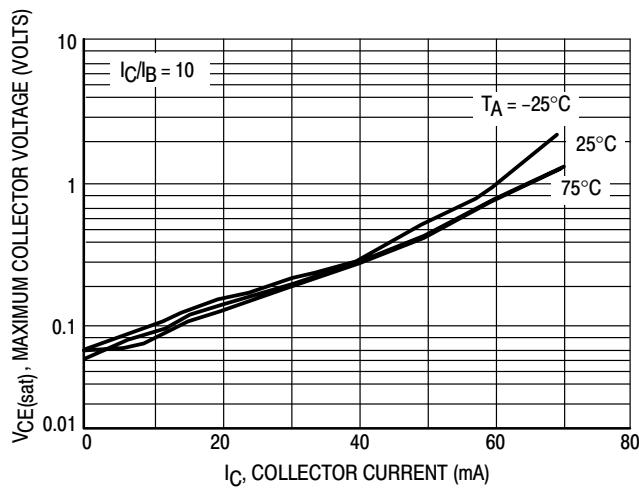


Figure 7.  $V_{CE(sat)}$  versus  $I_C$

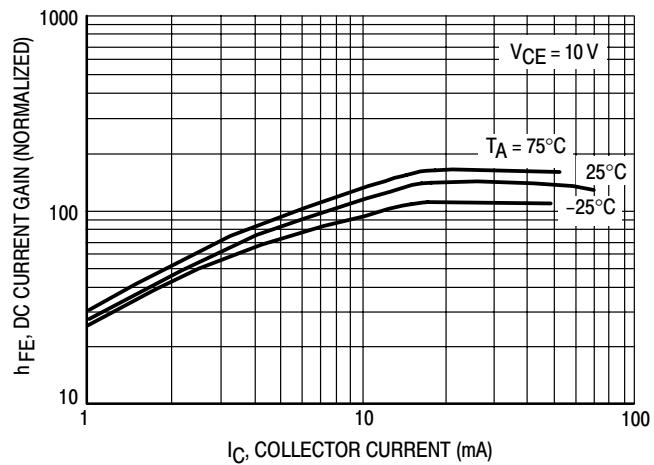


Figure 8. DC Current Gain

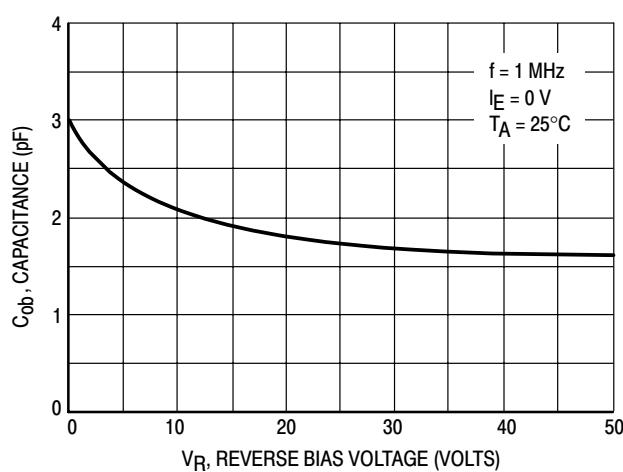


Figure 9. Output Capacitance

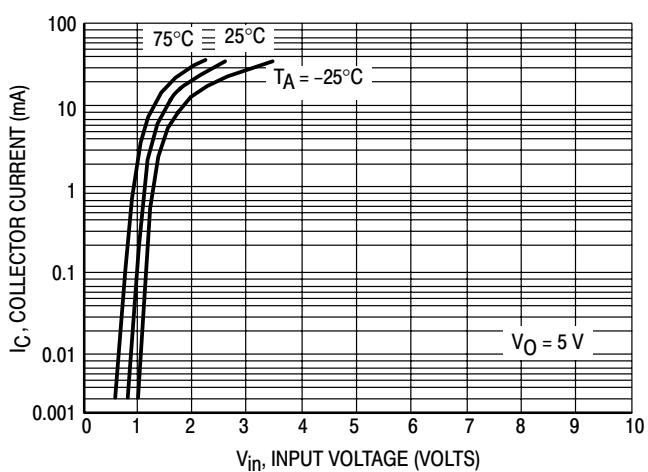


Figure 10. Output Current versus Input Voltage

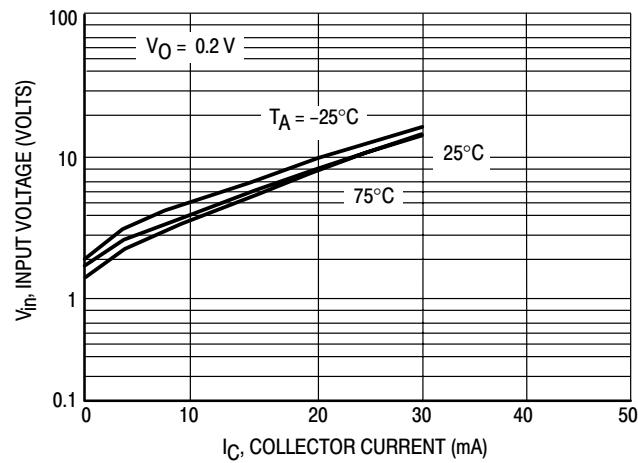


Figure 11. Input Voltage versus Output Current



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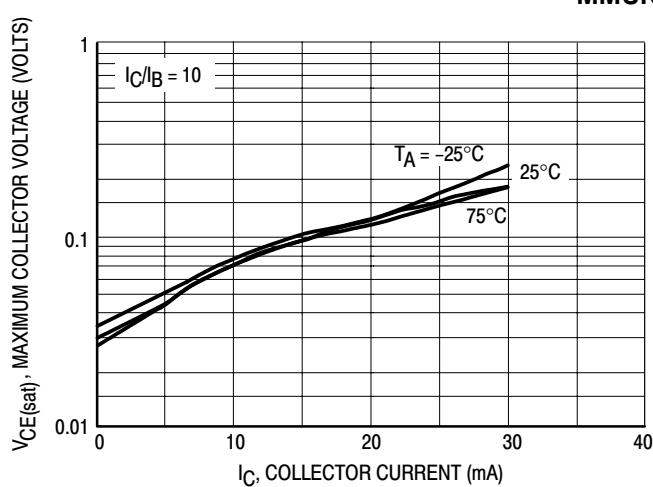


Figure 12.  $V_{CE(sat)}$  versus  $I_C$

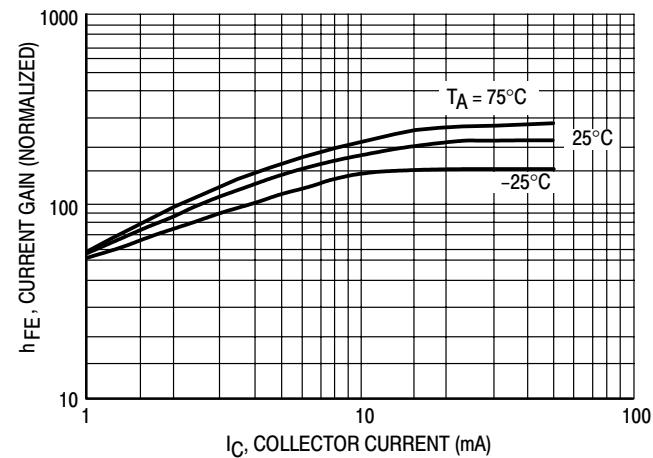


Figure 13. DC Current Gain

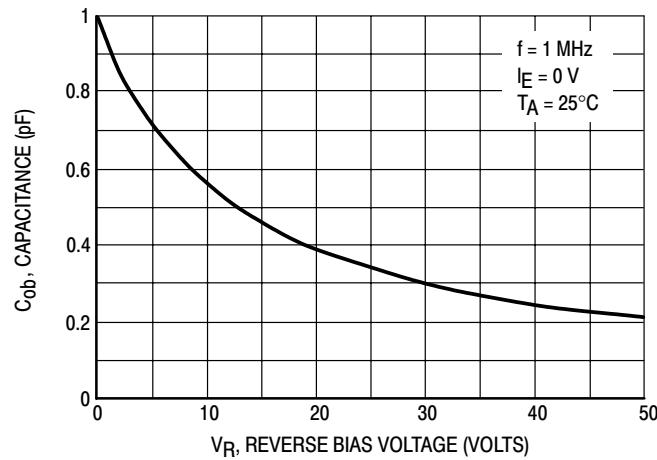


Figure 14. Output Capacitance

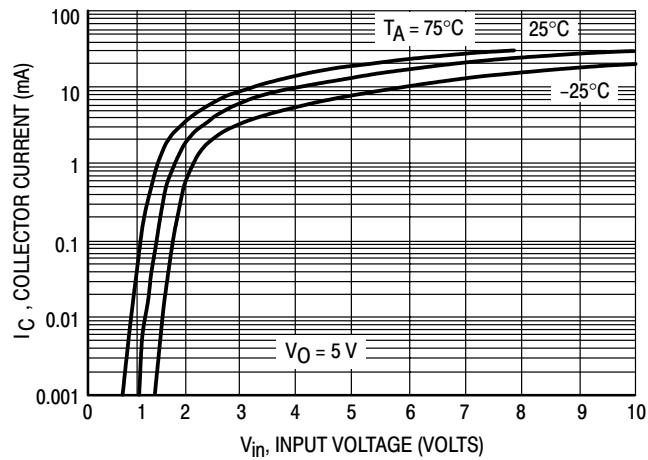


Figure 15. Output Current versus Input Voltage

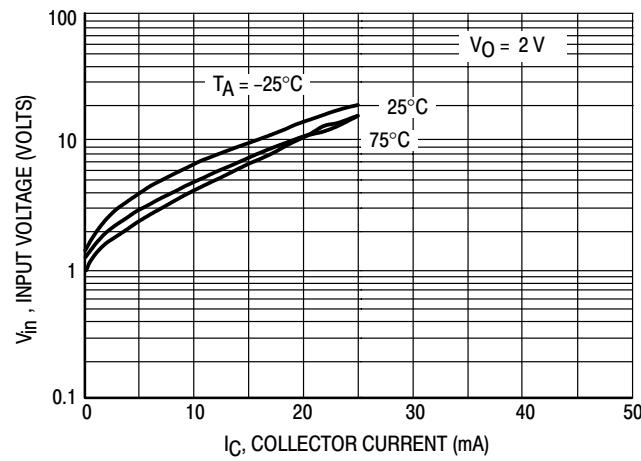


Figure 16. Input Voltage versus Output Current



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MMUN2114

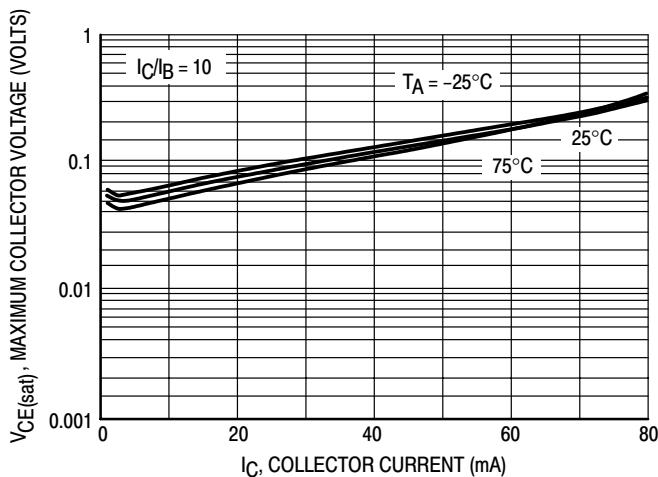


Figure 17.  $V_{CE(\text{sat})}$  versus  $I_C$

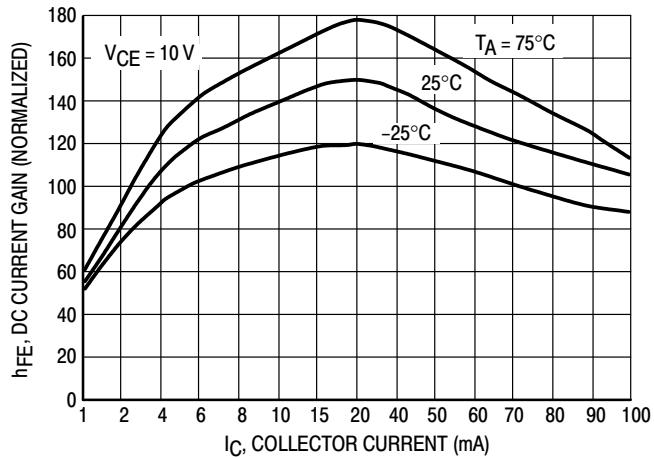


Figure 18. DC Current Gain

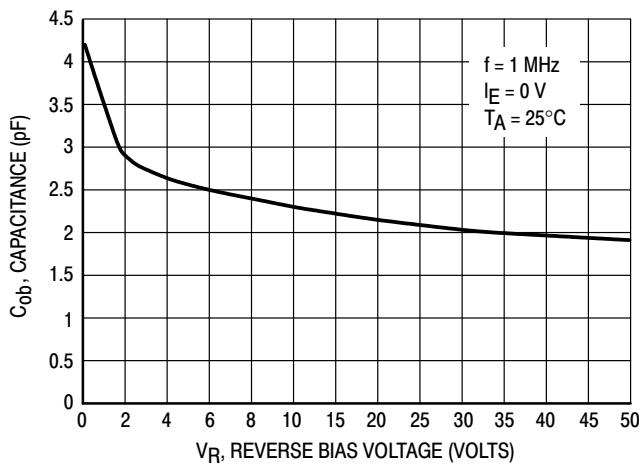


Figure 19. Output Capacitance

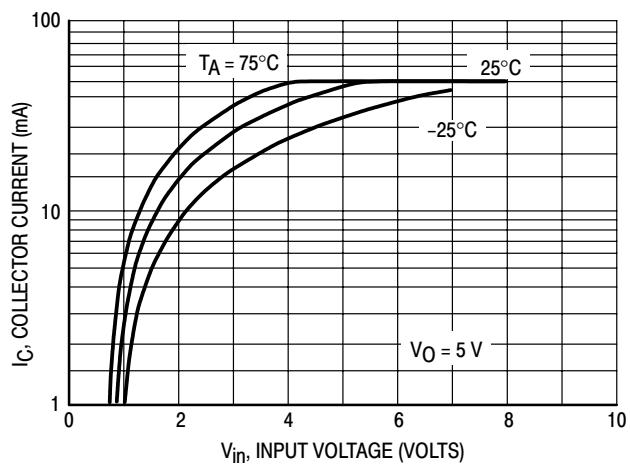


Figure 20. Output Current versus Input Voltage

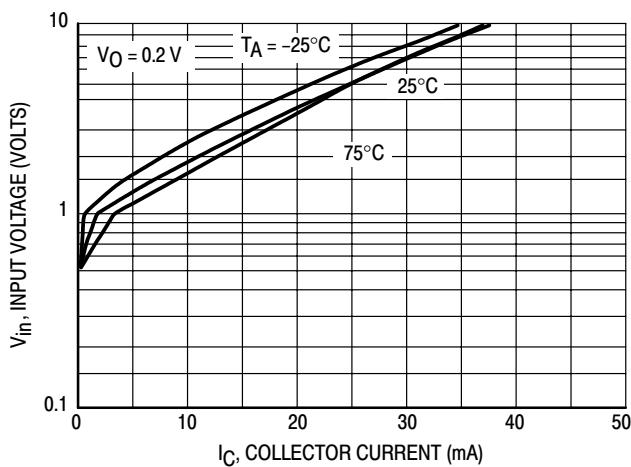


Figure 21. Input Voltage versus Output Current

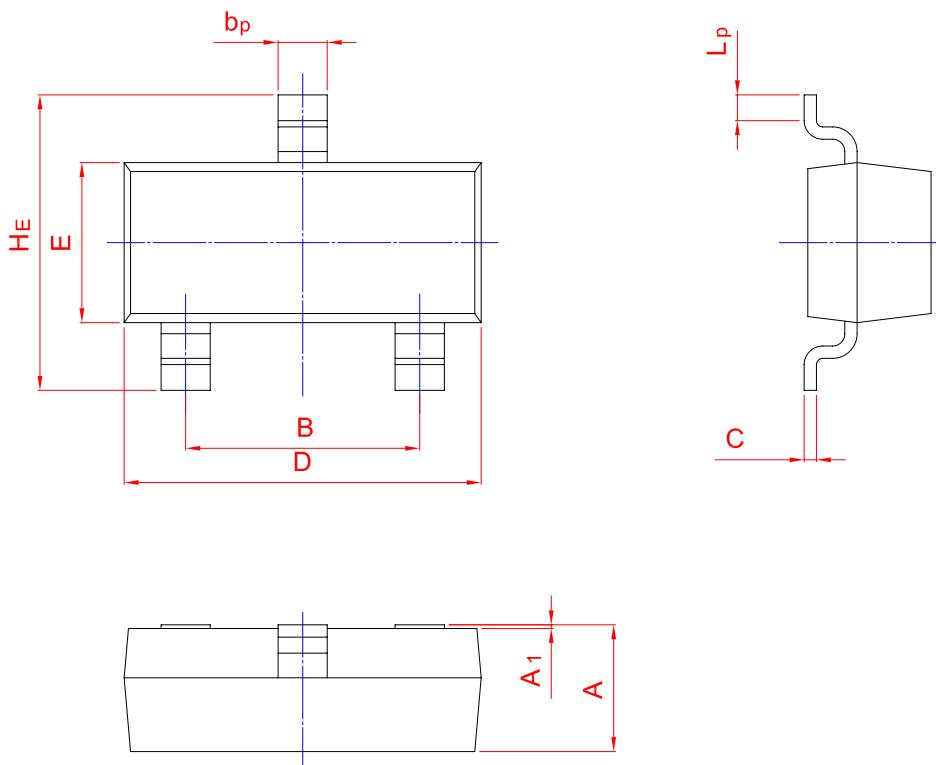


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## PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b <sub>p</sub>	C	D	E	H <sub>E</sub>	A <sub>1</sub>	L <sub>p</sub>
mm	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20